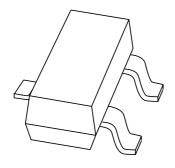
DISCRETE SEMICONDUCTORS

DATA SHEET



BC849; BC850 NPN general purpose transistors

Product specification
Supersedes data of 1998 Aug 06

1999 Apr 08





NPN general purpose transistors

BC849; BC850

FEATURES

• Low current (max. 100 mA)

• Low voltage (max. 45 V).

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

NPN transistor in a SOT23 plastic package. PNP complements: BC859 and BC860.

MARKING

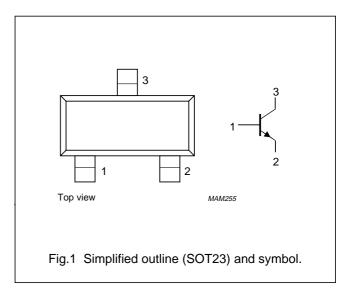
TYPE NUMBER	MARKING CODE ⁽¹⁾	TYPE NUMBER	MARKING CODE ⁽¹⁾		
BC849B	2B*	BC850B	2F*		
BC849C	2C*	BC850C	2G*		

Note

* = p : Made in Hong Kong.
 * = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BC849		_	30	V
	BC850		_	50	V
V _{CEO}	collector-emitter voltage	open base			
	BC849		_	30	V
	BC850		_	45	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	100	mA
I _{CM}	peak collector current		_	200	mA
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN general purpose transistors

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

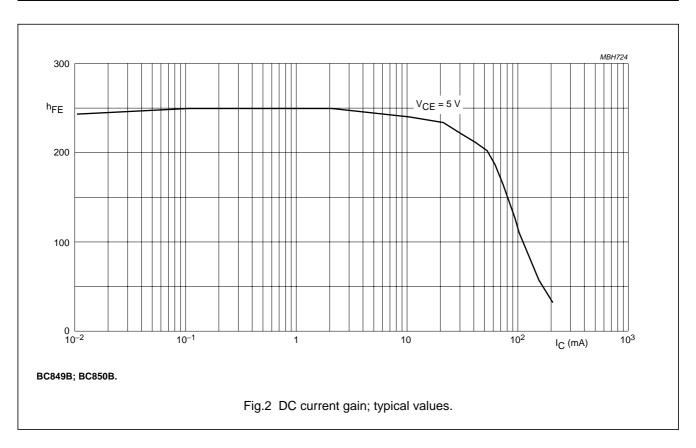
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	_	_	15	nA
		I _E = 0; V _{CB} = 30 V; T _j = 150 °C	_	_	5	μΑ
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V	_	_	100	nA
h _{FE}	DC current gain	$I_C = 10 \mu A; V_{CE} = 5 V;$				
	BC849B; BC850B	see Figs 2 and 3	_	240	-	
	BC849C; BC850C		_	450	-	
	DC current gain	$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V};$				
	BC849B; BC850B	see Figs 2 and 3	200	290	450	
	BC849C; BC850C		420	520	800	
V _{CEsat}	collector-emitter saturation	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	90	250	mV
	voltage	I _C = 100 mA; I _B = 5 mA	_	200	600	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = 10 \text{ mA}$; $I_B = 0.5 \text{ mA}$; note 1	_	700	_	mV
		$I_C = 100 \text{ mA}$; $I_B = 5 \text{ mA}$; note 1	_	900	_	mV
V_{BE}	base-emitter voltage	$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}; \text{ note } 2$	580	660	700	mV
		$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}; \text{ note 2}$	_	_	770	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$	_	2.5	_	pF
C _e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = 500 \text{ mV}$; $f = 1 \text{ MHz}$	_	11	_	pF
f _T	transition frequency	$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$	100	_	_	MHz
F	noise figure	I_C = 200 μA; V_{CE} = 5 V; R_S = 2 kΩ; f = 10 Hz to 15.7 kHz	_	_	4	dB
		I_C = 200 μA; V_{CE} = 5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz	_	_	4	dB

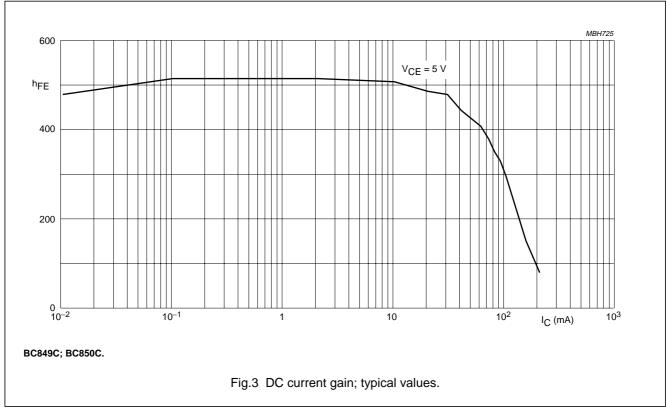
Notes

- 1. V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.
- 2. $V_{\mbox{\footnotesize{BE}}}$ decreases by about 2 mV/K with increasing temperature.

NPN general purpose transistors

BC849; BC850





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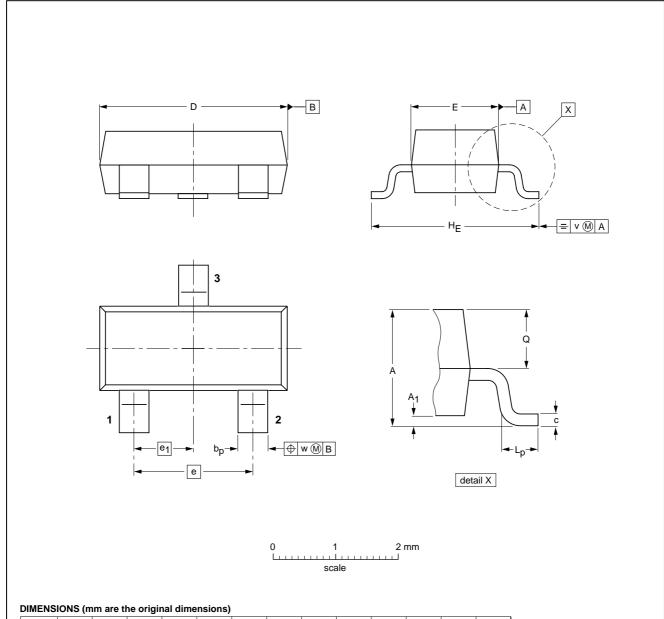
NPN general purpose transistors

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



UNIT	Α	A ₁ max.	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT23					97-02-28

NPN general purpose transistors

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

NPN general purpose transistors

BC849; BC850

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